

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("20020061658").PN.	US-PGPUB; USOCR	OR	OFF	2005/01/29 07:33
L2	10	(("20030203622") or ("20020061658") or ("5310700") or ("5447887") or ("6413805") or ("6489230") or ("6004847") or ("5665620") or ("4376672") or ("6180457")).PN.	US-PGPUB; USPAT	OR	OFF	2005/01/29 07:42
S1	1	438/255,258,201,261,257,756,757, 724.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) same ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:10
S2	4	438/255,258,201,261,257,756,757, 724.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:11
S3	0	438/255,258,201,261,257,756,757, 724.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) with ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:10
S4	9	"438"/\$.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) with ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:13
S5	10	"438"/\$.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) same ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:15
S6	32	"438"/\$.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:16
S7	36	"257"/\$.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:10
S8	182	semiconductor and ((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 11:09

S9	20	semiconductor and (((oxide adj nitride adj silicon) or ("ONS")) with ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:10
S10	22	semiconductor and (((oxide adj nitride adj silicon) or ("ONS")) same ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:10
S17	3	(("6004847") or ("5104819") or ("6274428")).PN.	USPAT; USOCR	OR	OFF	2004/09/10 13:11
S18	524	(438/255).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 10:08
S19	479	(438/258).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 10:10
S20	271	(438/261).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 10:10
S21	1104	(438/257).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 10:10
S22	450	(438/756).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 10:11
S23	116	(438/757).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 10:11

S24	308	(438/724).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 10:11
S25	3039	438/255,258,201,261,257,756,757, 724.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 10:15
S26	14	438/255,258,201,261,257,756,757, 724.ccls. and (ONS or (oxide adj nitride adj silicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 09:06
S27	1	438/255,258,201,261,257,756,757, 724.ccls. and ((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 10:18
S28	24	(ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/26 14:00
S29	13	((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 10:07
S30	8	("("6004847") or ("5104819") or ("6274428") or ("6180457") or ("6429470") or ("6318267") or ("5572050") or ("4775549")).PN.	USPAT; USOCR	OR	OFF	2003/04/07 12:58
S31	20	((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))) and (photoresist or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 08:00
S32	10	(((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))) and (photoresist or mask)) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 10:10
S33	191	(438/201).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/04 11:17

S34	0	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon)) same (photoresist or mask)) and (re-oxidiz\$6 or (second adj oxidiz\$6))	USPAT; JPO	OR	ON	2003/04/07 12:34
S35	0	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6))	USPAT; JPO	OR	ON	2003/04/07 12:38
S36	0	(ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon)) and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6)) and semiconductor	USPAT; JPO	OR	ON	2003/04/07 12:38
S37	66	(ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))	USPAT; JPO	OR	ON	2003/04/07 12:38
S38	80283	(ONO or (oxide adj nitride adj oxide)) or (ONS or (oxide adj nitride adj silicon))	USPAT; JPO	OR	ON	2003/04/07 12:38
S39	23	(ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon))	USPAT; JPO	OR	ON	2003/04/07 12:38
S40	0	((ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6))	USPAT; JPO	OR	ON	2003/04/07 12:39
S41	0	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6))	USPAT; JPO	OR	ON	2003/04/07 12:41
S42	11	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and semiconductor	USPAT; JPO	OR	ON	2003/04/07 12:40
S43	22	((ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and semiconductor	USPAT; JPO	OR	ON	2003/04/07 12:40

S44	36	((ONO or (oxide adj nitride adj oxide)) or (ONS or (oxide adj nitride adj silicon)) ) and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6))	USPAT; JPO	OR	ON	2003/04/07 12:40
S45	0	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon)) ) and (photoresist or mask) and (second adj oxidiz\$6)	USPAT; JPO	OR	ON	2003/04/07 12:41
S46	0	((ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon)) ) and (photoresist or mask) and (second adj oxidiz\$6)	USPAT; JPO	OR	ON	2003/04/07 12:41
S47	10	(("5756376") or ("5770467") or ("6318267") or ("6004847") or ("6429470") or ("6180457") or ("5104819") or ("5572050") or ("6472259") or ("4775549")).PN.	USPAT; USOCR	OR	OFF	2003/04/08 09:24
S48	1	("5650344").PN.	USPAT; USOCR	OR	OFF	2003/04/08 09:37
S49	5	(("5650344") or ("4698787") or ("4543597") or ("5049514") or ("5083172")).PN.	USPAT; USOCR	OR	OFF	2003/04/08 09:38
S50	8	(("6225162") or ("6388305") or ("6168987") or ("6133602") or ("5591681") or ("5436481") or ("6133093") or ("6096604")).PN.	USPAT; USOCR	OR	OFF	2003/04/18 13:51
S51	9	(("6225162") or ("6388305") or ("6168987") or ("6133602") or ("5591681") or ("5436481") or ("6133093") or ("6096604") or ("5572050")).PN.	USPAT; USOCR	OR	OFF	2003/04/18 15:09
S52	1	("6004847").PN.	USPAT; USOCR	OR	OFF	2003/09/30 13:31
S53	150	"438"/\$.ccls. and (oxide adj nitride adj silicon) and (photoresist or resist or mask) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 13:38
S54	100	"438"/\$.ccls. and (oxide adj nitride adj silicon) and (photoresist) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 10:58
S55	21	"438"/\$.ccls. and ((oxide adj nitride adj silicon) same (photoresist)) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 11:08

S56	13829	"438"/\$.ccls. and ((silicon) same (photoresist)) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 13:35
S57	13	438/255,258,201,261,257,756,757, 724.ccls. and (ONS or (oxide adj nitride adj silicon)) and (photoresist or resist or mask) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 11:11
S58	3	438/255,258,201,261,257,756,757, 724.ccls. and ((oxide adj nitride adj silicon) same (photoresist or resist or mask)) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 11:20
S59	1	("4376672").PN.	USPAT; USOCR	OR	OFF	2003/09/30 13:43
S60	982	438/255,258,201,261,257,756,757, 724.ccls. and ((silicon) same (photoresist)) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 13:35
S61	265	"438"/\$.ccls. and (ONS or (oxide adj nitride adj silicon)) and (photoresist or resist or mask) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 07:57
S62	10826	nguyen.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 13:38
S63	51	nguyen.inv. and (bich-yen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 13:38
S64	51	(nguyen.inv. and (bich-yen)) and motorola	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/30 13:38
S65	2	(("4376672") or ("5665620")).PN.	USPAT; USOCR	OR	OFF	2003/09/30 13:49
S66	9	(("4376672") or ("5665620") or ("6472259") or ("5104819") or ("6180457") or ("6168987") or ("5591681") or ("6096604") or ("5358892")).PN.	USPAT; USOCR	OR	OFF	2003/09/30 14:02
S67	1	("20020117736").PN.	US-PGPUB; USOCR	OR	OFF	2003/09/30 14:07

S68	18265	"438"/\$.ccls. and (ONS or (oxide same nitride same silicon)) and (photoresist or resist or mask) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 07:58
S69	2092	438/255,258,201,261,257,756,757, 724.ccls. and (ONS or (oxide same nitride same silicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 07:59
S70	2090	438/255,258,201,261,257,756,757, 724.ccls. and (oxide same nitride same silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 07:59
S71	585	438/255,258,201,261,257,756,757, 724.ccls. and ((oxide same nitride same silicon) same photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 08:01
S72	537	438/255,258,201,261,257,756,757, 724.ccls. and ((oxide same nitride same silicon) same photoresist) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 08:09
S73	537	438/255,258,201,261,257,756,757, 724.ccls. and ((ONS or (oxide same nitride same silicon)) same photoresist) and @ad<="20011130"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 08:25
S74	0	438/255,258,201,261,257,756,757, 724.ccls. same (high adj voltage adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 14:26
S75	11	438/255,258,201,261,257,756,757, 724.ccls. and (high adj voltage adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 14:27
S76	11	438/255,258,201,261,257,756,757, 724.ccls. and (high adj voltage adj oxide) and @ad<="20011120"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/01 14:27
S77	36	((ONS") or (oxide adj nitride adj silicon)) same ((ONO") or (oxide adj nitride adj oxide)) and @ad<="20011120"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/26 14:01

S78	19	((oxide adj nitride adj silicon) or ("ONS")) with ((oxide adj nitride adj oxide) or ("ONO")) and @ad<="20011120"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/26 14:03
S79	36	((oxide adj nitride adj silicon) or ("ONS")) same ((oxide adj nitride adj oxide) or ("ONO")) and @ad<="20011120"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 07:07
S80	0	"20020061658".URPN.	USPAT	OR	ON	2004/07/27 07:02
S81	1689	((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO")) and @ad<="20011120"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 07:09
S82	159	((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO")) and @ad<="20011120" and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 07:10